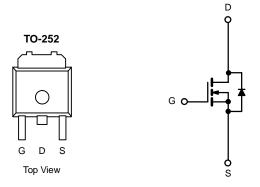


SSM85T03GH-VB Datasheet N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, e}	Q _g (Typ)			
30	0.002 at V _{GS} = 10 V	100	72 nC			
30	0.003 at V _{GS} = 4.5 V	90	12110			



N-Channel MOSFET

FEATURES

- Trench Power MOSFET
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter		Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage		V _{GS}		± 20
	T _C = 25 °C		100 ^{a, e}	
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 70 °C		80 ^e	
Continuous Diam Current (1 j = 173 °C)	T _A = 25 °C	I _D	35.8 ^{b, c}	A
	T _A = 70 °C		27 ^{b, c}	^
Pulsed Drain Current	I _{DM}	300		
Avalanche Current Pulse L = 0.1 ml		I _{AS}	39	
Single Pulse Avalanche Energy		E _{AS}	94.8	mJ
Continuous Source-Drain Diode Current	T _C = 25 °C		90 ^{a, e}	A
Continuous Source-Drain Diode Current	T _A = 25 °C	l _s —	3.13 ^{b, c}	
	T _C = 25 °C		235 ^a	
Marianas Davies Discipation	T _C = 70 °C	ь	165	14/
Maximum Power Dissipation	T _A = 25 °C	P _D	3.75 ^{b, c}	W
	T _A = 70 °C		2.63 ^{b, c}	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Тур.	Max.	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	C/ VV	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- b. Striate informed on 1 X 1 114 board.
 c. t = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ 3				V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L = 250 µA		35		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 7.5		mv/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
7 0		V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α	
	В	V _{GS} = 10 V, I _D = 38.8 A		0.002		Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 37 \text{ A}$		0.003			
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 38.8 \text{ A}$		160		S	
Dynamic ^b							
Input Capacitance	C _{iss}			5201		pF	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1525			
Reverse Transfer Capacitance	C _{rss}			770			
Total Cata Charge	0	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 38.8 \text{ A}$		151	227	nC	
Total Gate Charge	Q_g			71.5	103		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 28.8 \text{ A}$		30			
Gate-Drain Charge	Q_{gd}			24			
Gate Resistance	R_g	f = 1 MHz		1.4	2.1	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 24 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		70	105		
Fall Time	t _f			10	15	ne	
Turn-On Delay Time	t _{d(on)}			55	83	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.67 Ω		180	270		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 22.5~A,~V_{GEN}=4.5~V,~R_g=1~\Omega$		55	83		
Fall Time	t _f			12	18		
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			120	Δ	
Pulse Diode Forward Current ^a	I _{SM}				120	Α	
Body Diode Voltage	V_{SD}	I _S = 22 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		70.2	105	nC	
Reverse Recovery Fall Time	t _a	1F - 20 A, αι/αι = 100 Αγμ5, 1J = 25 °C		27			
Reverse Recovery Rise Time	t _b			25		ns	

Notes:

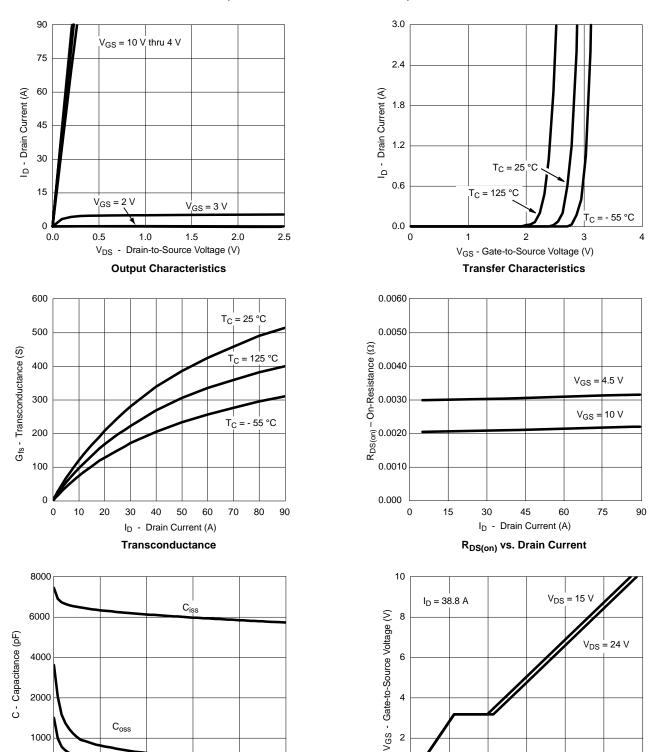
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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 C_{rss}

Q_g - Total Gate Charge (nC)

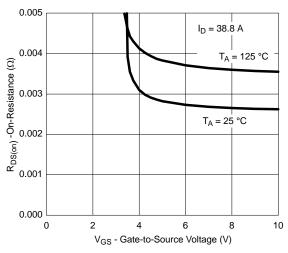
Gate Charge



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



 $\rm R_{\rm DS(on)}$ vs. $\rm V_{\rm GS}$ vs. Temperature



Forward Diode Voltage vs. Temperature



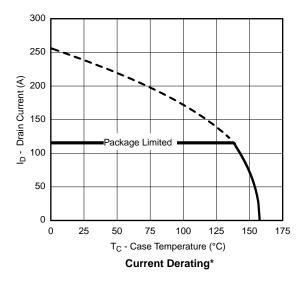
Threshold Voltage



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

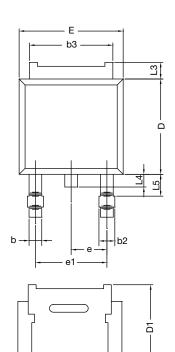


Normalized Thermal Transient Impedance, Junction-to-Case

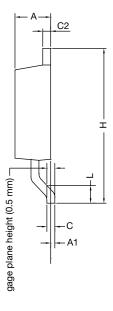
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TO-252AA CASE OUTLINE



E1



	MILLIN	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.

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